

L26 ANSWER 17 OF 17 INSPEC COPYRIGHT 2002 IEE  
 AN 1990:3654158 INSPEC DN A90090924; B90042737  
 TI Growth of single crystal **GaN** substrate using **hydride vapor** phase epitaxy.  
 AU Naniwae, K.; Itoh, S.; Amano, H.; Itoh, K.; Hiramatsu, K.; Akasaki, I.  
 (Dept. of Electron., Nagoya Univ., Japan)  
 SO Journal of Crystal Growth (Jan. 1990) vol.99, no.1-4, pt.1, p.381-4. 10 refs.  
 Price: CCCC 0022-0248/90/\$03.50  
 CODEN: JCRGAE ISSN: 0022-0248  
 Conference: Ninth International Conference on Crystal Growth: ICCG -9.  
 Sendai, Japan, 20-25 Aug 1989  
 Sponsor(s): Sci. Council Japan; Japan Soc. Appl. Phys.; Japanese Assoc. Crystal Growth  
 DT Conference Article; Journal  
 TC Experimental  
 CY Netherlands  
 LA English  
 AB **Hydride vapor** phase epitaxy (**HVPE**) was performed to prepare thick **GaN** films. It is found that (1) surface **treatment** of the sapphire substrate by the Ga+HCl gas just before the growth of **GaN** film reduces the pit density and improves the crystalline quality of the epitaxial **GaN** film, (2) the photoluminescence (PL) spectrum measured at 4.2 K shows the free A-exciton line and a narrow I2 line, indicating that the **GaN** crystals prepared in the study are of high purity and high crystalline quality, and (3) the magnitude of the strain of the homo-epitaxially grown **GaN** on a thick **GaN** buffer layer thus prepared is less than half that of a hetero-epitaxially grown **GaN** on sapphire. These results show that high quality, thick single crystals of **GaN** can be prepared homo-epitaxially using **HVPE**.  
 CC A8115H Chemical vapour deposition; A6855 Thin film growth, structure, and epitaxy; A7865J Nonmetals; A7855D Tetrahedrally bonded nonmetals; B0510D Epitaxial growth; B2520D II-VI and III-V semiconductors  
 CT EXCITONS; GALLIUM COMPOUNDS; III-V SEMICONDUCTORS; INTERNAL STRESSES; LUMINESCENCE OF INORGANIC SOLIDS; PHOTOLUMINESCENCE; SEMICONDUCTOR EPITAXIAL LAYERS; SEMICONDUCTOR GROWTH; VAPOUR PHASE EPITAXIAL GROWTH  
 ST photoluminescence spectrum; III-V semiconductor; **hydride vapor phase epitaxy; thick GaN films; surface treatment; sapphire substrate; pit density; crystalline quality; free A-exciton line; homo-epitaxially grown GaN; thick GaN buffer layer; 4.2 K; single crystal GaN substrate; Al2O3**  
 CHI Al2O3 sur, Al2 sur, Al sur, O3 sur, O sur, Al2O3 bin, Al2 bin, Al bin, O3 bin, O bin; GaN sur, Ga sur, N sur, GaN bin, Ga bin, N bin  
 PHP temperature 4.2E+00 K  
 ET Ga\*N; GaN; Ga cp; cp; N cp; Cl\*Ga\*H; HCl; H cp; Cl cp; Ga+HCl; I2; V; Al\*O; Al2O3; Al cp; O cp; Al2O; Al; O; Ga; N

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